Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Supplementary materials

for

Spontaneous off-stoichiometry as the knob to control dielectric properties of gapped metals

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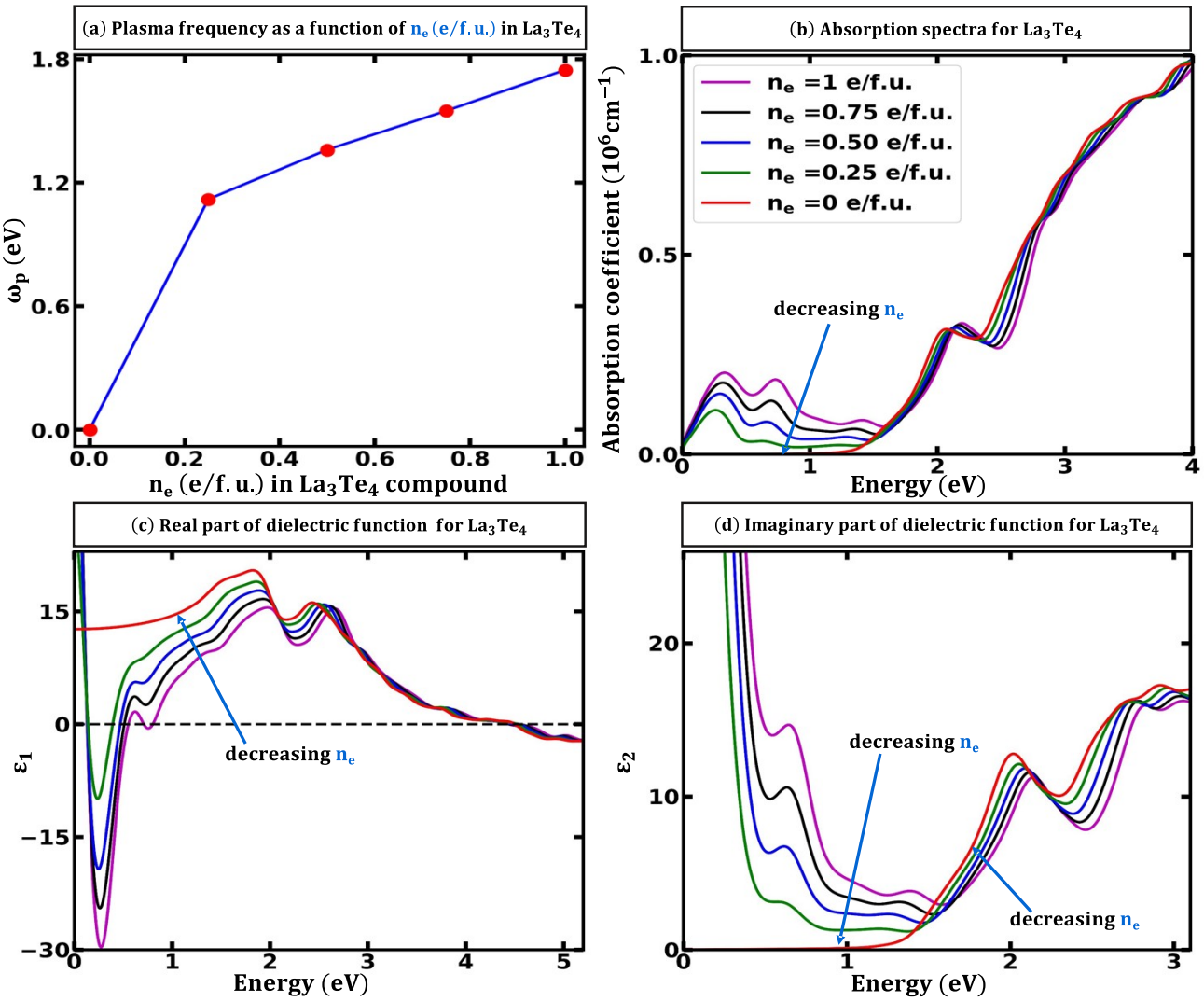

Figure S1: (a) Plasma frequency as a function of different numbers of electrons in La_3Te_4. (b) Absorption spectra for La_3Te_4 with different number of electrons considering superposition of both interband and intraband transitions. (c) Real and (d) imaginary part of dielectric function for a different number of electrons per formula unit (n_e/f.u.) in the conduction band of La_3Te_4. The results are shown for a ridged shift of the Fermi level.